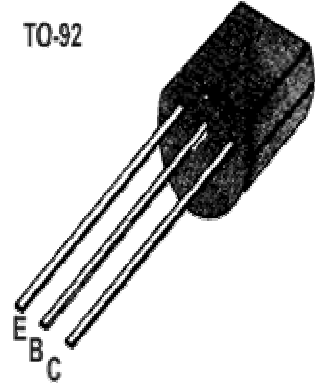


■■ APPLICATION: General purpose application, Switching application.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-150	mA
Collector Power Dissipation	P _c	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

TO-92



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	200		600		V _{CE} = -5 V, I _c = -1 mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} =-50 V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5 V, I _c =0
Collector-Base Breakdown Voltage	BV _{CBO}	-50			V	I _c =-0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _c =-1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.1	-0.3	V	I _c =-100 mA, I _B =-10 mA
Gain bandwidth product	f _r	60			MHz	I _c = -1 mA, V _{CE} =-10V, f= 100 MHz
Common Base Output Capacitance	C _{ob}		4.0	7.0	PF	V _{CB} = -10V, I _E =0, f= 1 MHz
Noise Figure	N _F		1.0	10	dB	V _{CE} = -6 V, I _c =-0.1 mA, f=1KHz, R _g =10KΩ

■■ h_{FE} Classification

Classification

 h_{FE}

200~600